

采用增强型航天塑料的 TLV1704-SEP 2.2V 至 36V 耐辐射微功耗 四路比较器

1 特性

- VID V62/18613
- 耐辐射
 - 单粒子锁定 (SEL) 在 125°C 下的抗扰度可达 43MeV-cm²/mg
 - 在高达 30krad(Si) 的条件下无 ELDRS
 - 每个晶圆批次的 RLAT 总电离剂量 (TID) 高达 20krad(Si)
- 增强型航天塑料
 - 受控基线
 - 金线
 - NiPdAu 铅涂层
 - 同一组装和测试场所
 - 同一制造场所
 - 支持军用 (-55°C 至 125°C) 温度范围
 - 延长的产品生命周期
 - 延长的产品变更通知
 - 产品可追溯性
 - 采用增强型模具化合物实现低释气
- 电源电压范围: 2.2V 至 36V 或 ±1.1V 至 ±18V
- 低静态电流: 每个比较器 55μA
- 输入共模范围包括两个电源轨
- 低传播延迟: 560ns
- 低输入失调电压: 300μV
- 集电极开路输出:
 - 最多可高出负电源电压 36V 且不受电源电压影响
- 小型封装:
 - 四通道: TSSOP-14

2 应用范围

- 支持近地球轨道空间 应用
- 过压和欠压检测器
- 用于机载数据处理的卫星遥测和遥控
- 窗口比较器
- 过流检测器
- 过零检测器
- 航天系统监控

3 说明

TLV1704-SEP (四路) 器件具有宽电源电压范围、轨至轨输入、低静态电流和低传播延迟。所有这些特性均在一个行业标准的极小型封装中实现, 因此这些器件是目前市面上绝佳的通用比较器。

集电极开路输出带来了能够将输出拉至任意电压轨 (最多可高出负电源 36V) 且不受 TLV1704-SEP 电源电压影响的优势。

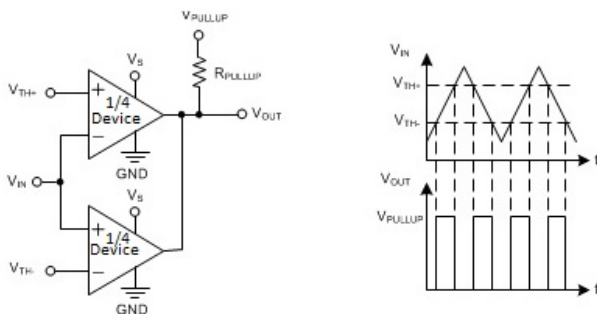
此器件是一款微功耗比较器。低输入失调电压、低输入偏置电流、低电源电流和集电极开路配置使 TLV1704-SEP 器件能够灵活处理从简单电压检测到驱动单个继电器的大部分应用。

器件信息⁽¹⁾

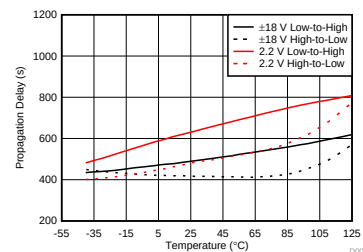
器件型号	等级	封装
TLV1704AMPWTPSEP	20krad(Si) RLAT	TSSOP (14)
TLV1704AMPWPSEP		

(1) 如需了解所有可用封装, 请参阅数据表末尾的封装选项附录。

TLV1704-SEP 用作窗口比较器



稳定传播延迟与温度



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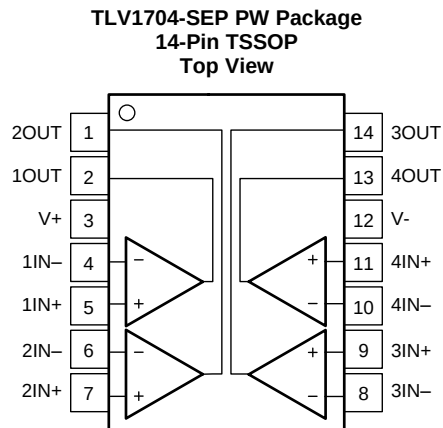
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4 修订历史记录

注：之前版本的页码可能与当前版本有所不同。

日期	修订版本	说明
2018 年 11 月	*	最初发布版本。

5 Pin Configuration and Functions



Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
IN+	—	I	Noninverting input.
1IN+	5	I	Noninverting input, channel 1.
2IN+	7	I	Noninverting input, channel 2.
3IN+	9	I	Noninverting input, channel 3.
4IN+	11	I	Noninverting input, channel 4.
IN–	—	I	Inverting input.
1IN–	4	I	Inverting input, channel 1.
2IN–	6	I	Inverting input, channel 2.
3IN–	8	I	Inverting input, channel 3.
4IN–	10	I	Inverting input, channel 4.
OUT	—	O	Output.
1OUT	2	O	Output, channel 1.
2OUT	1	O	Output, channel 2.
3OUT	14	O	Output, channel 3.
4OUT	13	O	Output, channel 4.
V+	3	—	Positive (highest) power supply.
V–	12	—	Negative (lowest) power supply.

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
Supply voltage			40 (±20)	V
Signal input pins	Voltage ⁽²⁾	$(V_{S-}) - 0.5$	$(V_{S+}) + 0.5$	V
	Current ⁽²⁾		±10	mA
Output short-circuit ⁽³⁾		Continuous		mA
Operating Junction temperature, T_J		–55	125	°C
Storage temperature, T_{stg}		–65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) Input pins are diode-clamped to the power-supply rails. Input signals that can swing more than 0.5 V beyond the supply rails must be current limited to 10 mA or less.
- (3) Short-circuit to ground; one comparator per package.

6.2 ESD Ratings

		VALUE	UNIT
$V_{(ESD)}$ Electrostatic discharge	Human-body model (HBM), per AEC Q100-002 ⁽¹⁾	±1000	V
	Charged-device model (CDM), per AEC Q100-011	±1000	

- (1) AEC Q100-002 indicates that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

	MIN	NOM	MAX	UNIT
Supply voltage $V_S = (V_{S+}) - (V_{S-})$	2.2 (±1.1)		36 (±18)	V
Specified temperature	–55		125	°C

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		TLV1704-SEP	UNIT
		PW (TSSOP)	
		14 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	128.1	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	56.5	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	69.9	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	9.1	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	69.3	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A	°C/W

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

6.5 Electrical Characteristics

at $T_A = -55^{\circ}\text{C}$ to 125°C , $V_S = 2.2\text{ V}$ to 36 V , $C_L = 15\text{ pF}$, $R_{\text{PULLUP}} = 5.1\text{ k}\Omega$, $V_{\text{CM}} = V_S / 2$, and $V_S = V_{\text{PULLUP}}$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFFSET VOLTAGE						
V _{OS}	Input offset voltage	T _A = 25°C, V _S = 2.2 V		±0.5	±3.5	mV
		T _A = 25°C, V _S = 36 V		±0.3	±2.5	mV
		T _A = –55°C to 125°C			±5.5	mV
dV _{OS} /dT	Input offset voltage drift	T _A = –55°C to 125°C		±4	±20	μV/°C
PSRR	Power-supply rejection ratio	T _A = 25°C		15	100	μV/V
		T _A = –55°C to 125°C		20		μV/V
INPUT VOLTAGE RANGE						
V _{CM}	Common-mode voltage range	T _A = –55°C to 125°C	(V–)		(V+)	V
INPUT BIAS CURRENT						
I _B	Input bias current	T _A = 25°C		5	15	nA
		T _A = –55°C to 125°C			20	nA
I _{OS}	Input offset current	T _A = 25°C		0.5		nA
C _{LOAD}	Capacitive load drive		See Typical Characteristics			
OUTPUT						
V _O	Voltage output swing from rail	I _O ≤ 4 mA, input overdrive = 100 mV, V _S = 36 V			1100	mV
		I _O = 0 mA, input overdrive = 100 mV, V _S = 36 V			700	mV
I _{SC}	Short circuit sink current	T _A = 25°C		20		mA
	Output leakage current	V _{IN+} > V _{IN–} , T _J = 25°C		70		nA
POWER SUPPLY						
V _S	Specified voltage range		2.2		36	V
I _Q	Quiescent current (per channel)	I _O = 0 A, T _A = 25°C		55	75	μA
		I _O = 0 A, T _A = –55°C to 125°C			100	μA

6.6 Switching Characteristics

at $T_A = -55^{\circ}\text{C}$ to 125°C , $V_S = 2.2\text{ V}$ to 36 V , $C_L = 15\text{ pF}$, $R_{\text{PULLUP}} = 5.1\text{ k}\Omega$, $V_{\text{CM}} = V_S / 2$, and $V_S = V_{\text{PULLUP}}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{pHL} Propagation delay time, high-to-low	Input overdrive = 100 mV, $T_A = 25^{\circ}\text{C}$		460		ns
t_{pLH} Propagation delay time, low-to-high	Input overdrive = 100 mV, $T_A = 25^{\circ}\text{C}$		560		ns
t_R Rise time	Input overdrive = 100 mV, $T_A = 25^{\circ}\text{C}$		365		ns
t_F Fall time	Input overdrive = 100 mV, $T_A = 25^{\circ}\text{C}$		240		ns

6.7 Typical Characteristics

at $T_A = 25^\circ\text{C}$, $V_S = 5\text{ V}$, $R_{\text{PULLUP}} = 5.1\text{ k}\Omega$, and input overdrive = 100 mV (unless otherwise noted)

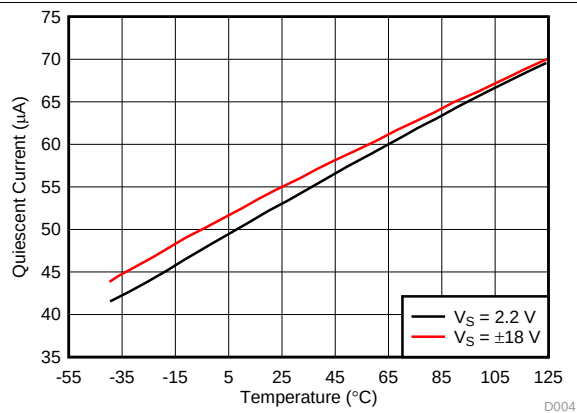


Figure 1. Quiescent Current vs Temperature

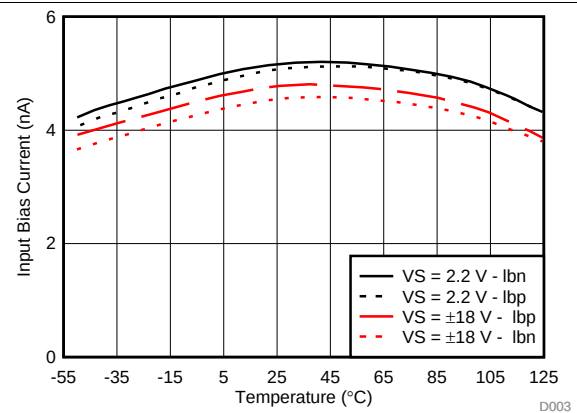


Figure 2. Input Bias Current vs Temperature

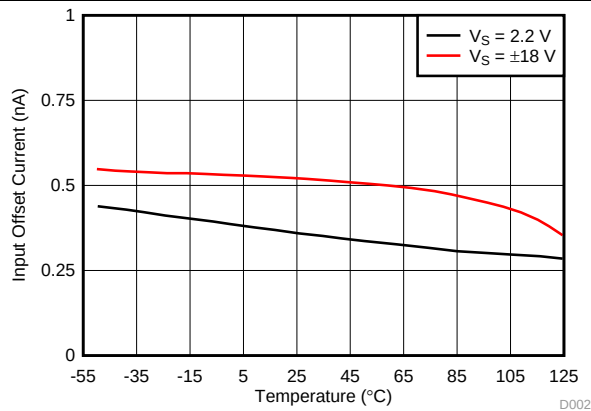


Figure 3. Input Offset Current vs Temperature

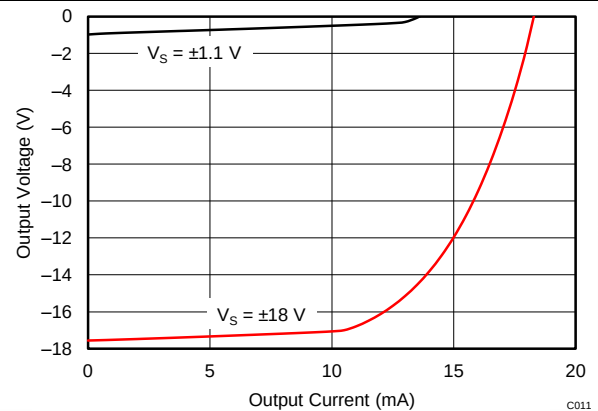


Figure 4. Output Voltage vs Output Current

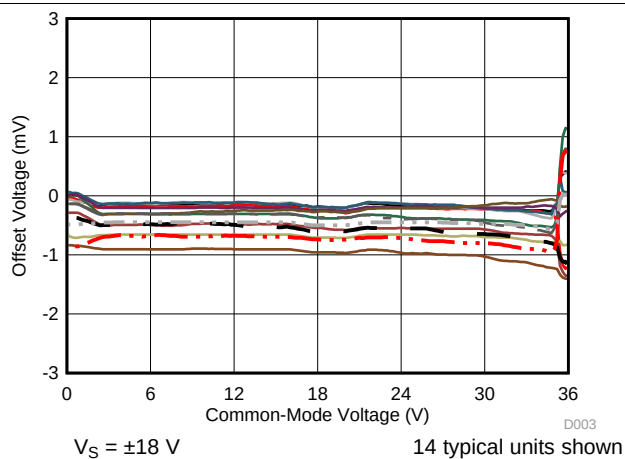


Figure 5. Offset Voltage vs Common-Mode Voltage

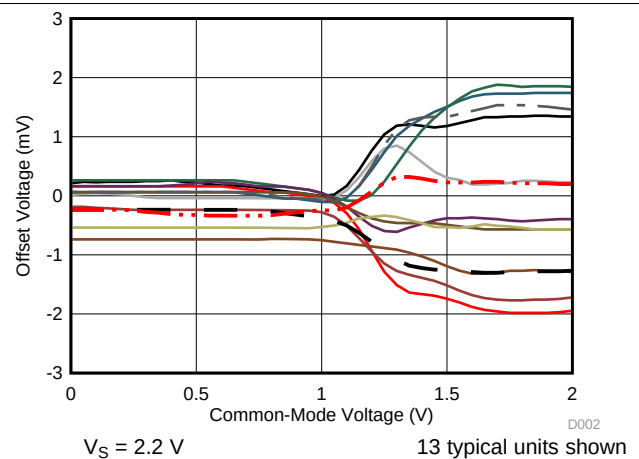


Figure 6. Offset Voltage vs Common-Mode Voltage

Typical Characteristics (continued)

at $T_A = 25^\circ\text{C}$, $V_S = 5\text{ V}$, $R_{\text{PULLUP}} = 5.1\text{ k}\Omega$, and input overdrive = 100 mV (unless otherwise noted)

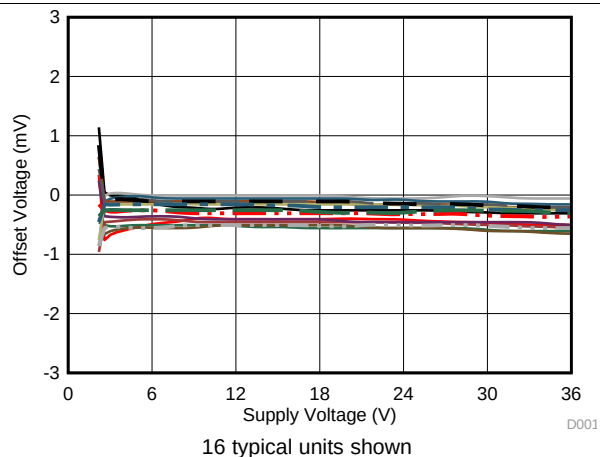


Figure 7. Offset Voltage vs Supply Voltage

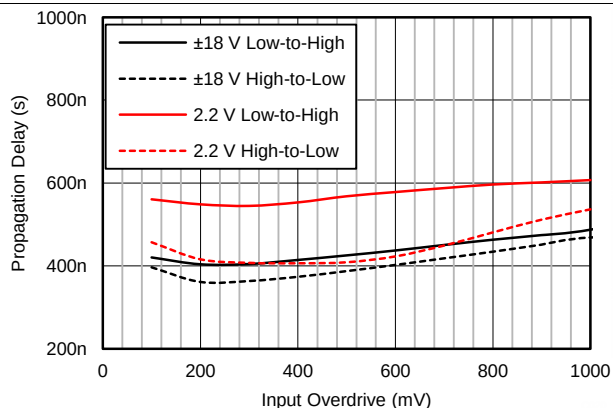


Figure 8. Propagation Delay vs Input Overdrive

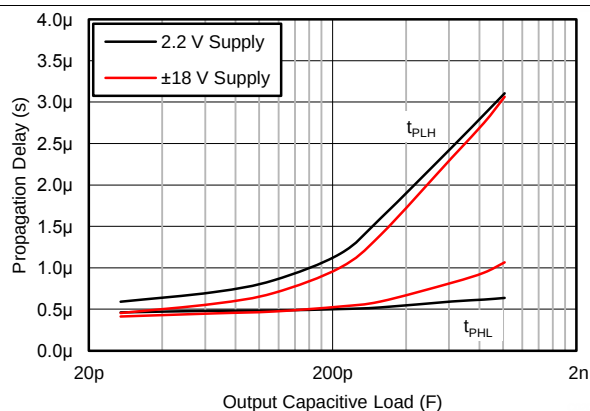


Figure 9. Propagation Delay vs Capacitive Load

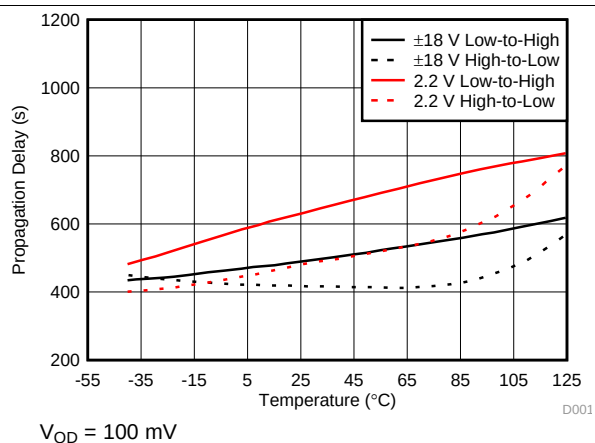


Figure 10. Propagation Delay vs Temperature

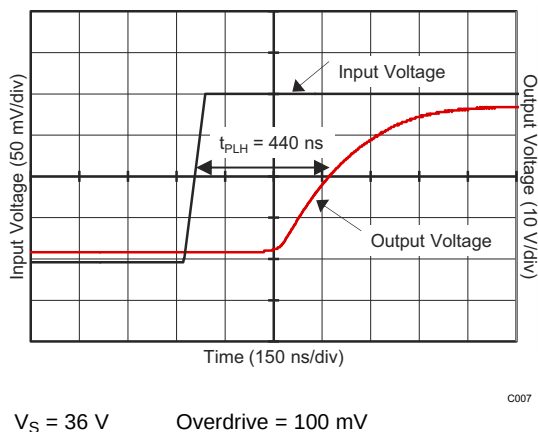


Figure 11. Propagation Delay (T_{PLH})

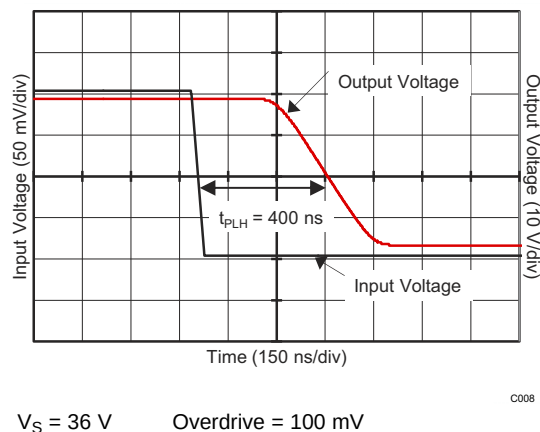
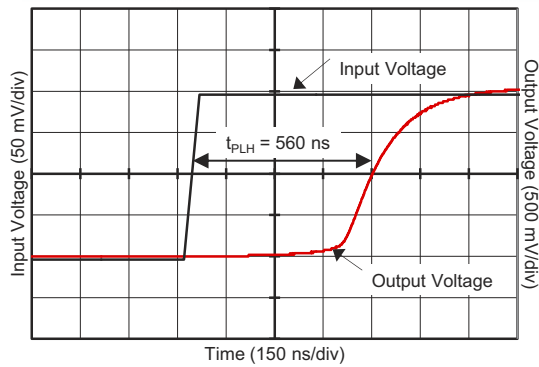


Figure 12. Propagation Delay (T_{PHL})

Typical Characteristics (continued)

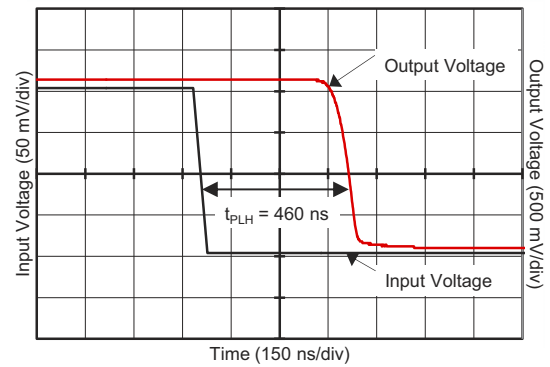
at $T_A = 25^\circ\text{C}$, $V_S = 5\text{ V}$, $R_{\text{PULLUP}} = 5.1\text{ k}\Omega$, and input overdrive = 100 mV (unless otherwise noted)



$V_S = 2.2\text{ V}$ Overdrive = 100 mV

C009

Figure 13. Propagation Delay (T_{pLH})



$V_S = 2.2\text{ V}$ Overdrive = 100 mV

C010

Figure 14. Propagation Delay (T_{pHL})

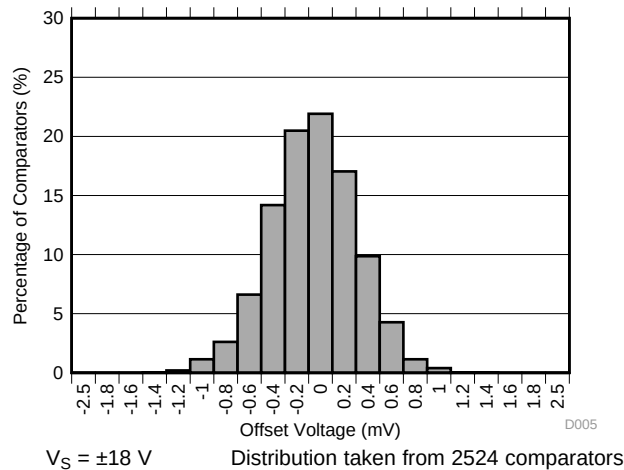


Figure 15. Offset Voltage Production Distribution

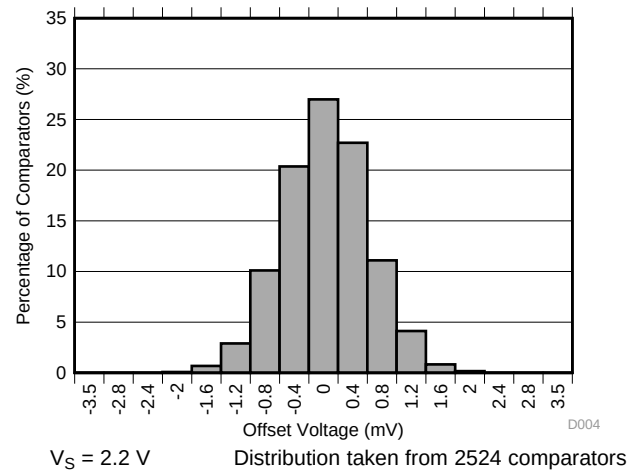


Figure 16. Offset Voltage Production Distribution

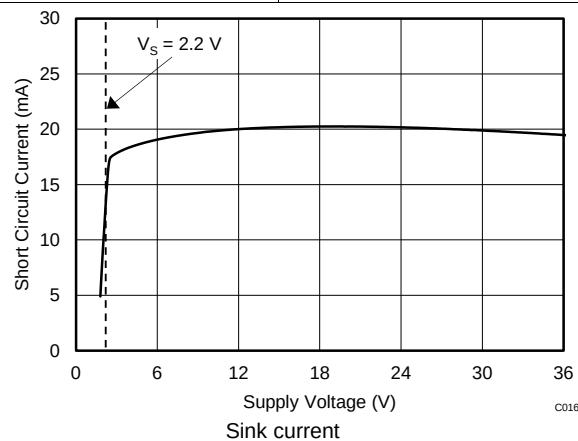


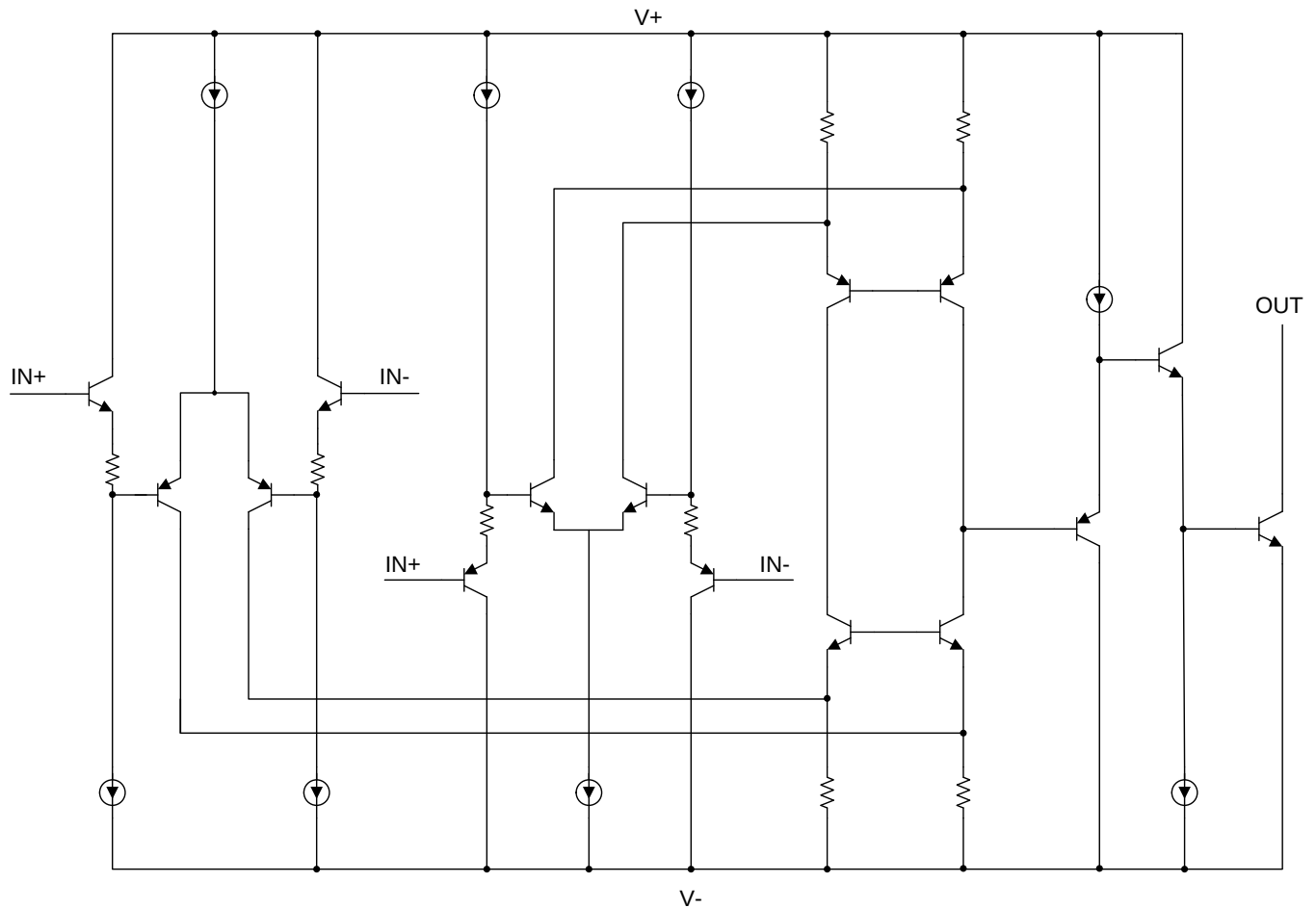
Figure 17. Short-Circuit Current vs Supply Voltage

7 Detailed Description

7.1 Overview

The TLV1704-SEP comparator features rail-to-rail input and output on supply voltages as high as 36 V. The rail-to-rail input stage enables detection of signals close to the supply and ground. The open-collector configuration allows the device to be used in wired-OR configurations, such as a window comparator. A low supply current of 55 μA per channel with small, space-saving packages, makes these comparators versatile for use in a wide range of applications, from portable to industrial.

7.2 Functional Block Diagram



7.3 Feature Description

7.3.1 Comparator Inputs

The TLV1704-SEP device is a rail-to-rail input comparator, with an input common-mode range that includes the supply rails. The TLV1704-SEP device is designed to prevent phase inversion when the input pins exceed the supply voltage. Figure 18 shows the TLV1704-SEP device response when input voltages exceed the supply, resulting in no phase inversion.

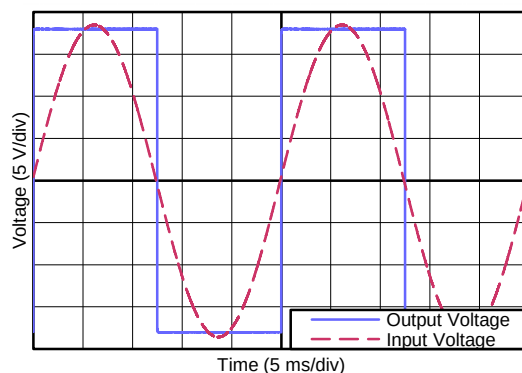


Figure 18. No Phase Inversion: Comparator Response to Input Voltage (Propagation Delay Included)

7.4 Device Functional Modes

7.4.1 Setting Reference Voltage

Using a stable reference is important when setting the transition point for the TLV1704-SEP device. The REF3333, as shown in Figure 19, provides a 3.3-V reference voltage with low drift and only 3.9 μ A of quiescent current.

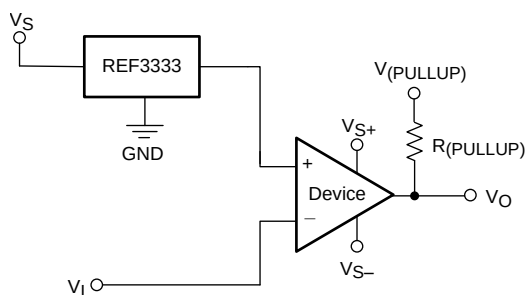


Figure 19. Reference Voltage for the TLV1704-SEP

8 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

8.1 Application Information

The TLV1704-SEP device can be used in a wide variety of applications, such as zero crossing detectors, window comparators, over and undervoltage detectors, and high-side voltage sense circuits.

8.2 Typical Application

Comparators are used to differentiate between two different signal levels. For example, a comparator differentiates between an overtemperature and normal-temperature condition. However, noise or signal variation at the comparison threshold causes multiple transitions. This application example sets upper and lower hysteresis thresholds to eliminate the multiple transitions caused by noise.

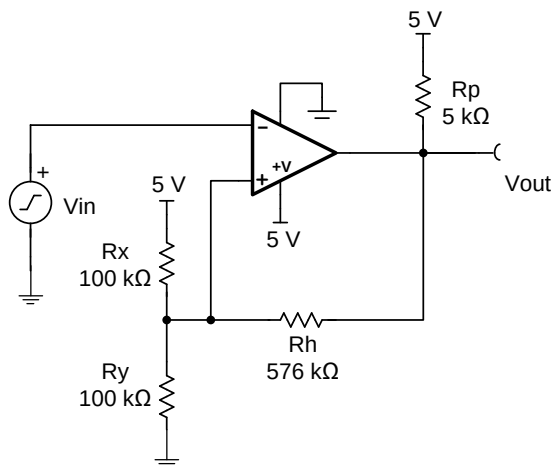


Figure 20. Comparator Schematic With Hysteresis

8.2.1 Design Requirements

The design requirements are as follows:

- Supply voltage: 5 V
- Input: 0 V to 5 V
- Lower threshold (V_L) = 2.3 V $\pm$ 0.1 V
- Upper threshold (V_H) = 2.7 V $\pm$ 0.1 V
- $V_H - V_L$ = 2.4 V $\pm$ 0.1 V
- Low-power consumption

Typical Application (continued)

8.2.2 Detailed Design Procedure

Make a small change to the comparator circuit to add hysteresis. Hysteresis uses two different threshold voltages to avoid the multiple transitions introduced in the previous circuit. The input signal must exceed the upper threshold (VH) to transition low, or below the lower threshold (VL) to transition high.

Figure 20 illustrates hysteresis on a comparator. Resistor Rh sets the hysteresis level. An open-collector output stage requires a pullup resistor (Rp). The pullup resistor creates a voltage divider at the comparator output that introduces an error when the output is at logic high. This error can be minimized if $R_h > 100 R_p$.

When the output is at a logic high (5 V), Rh is in parallel with Rx (ignoring Rp). This configuration drives more current into Ry, and raises the threshold voltage (VH) to 2.7 V. The input signal must drive above $V_H = 2.7$ V to cause the output to transition to logic low (0 V).

When the output is at logic low (0 V), Rh is in parallel with Ry. This configuration reduces the current into Ry, and reduces the threshold voltage to 2.3 V. The input signal must drive below $V_L = 2.3$ V to cause the output to transition to logic high (5 V).

For more details on this design and other alternative devices that can be used in place of the TLV1702, refer to Precision Design [TIPD144](#), *Comparator with Hysteresis Reference Design*.

8.2.3 Application Curve

Figure 21 shows the upper and lower thresholds for hysteresis. The upper threshold is 2.76 V and the lower threshold is 2.34 V, both of which are close to the design target.

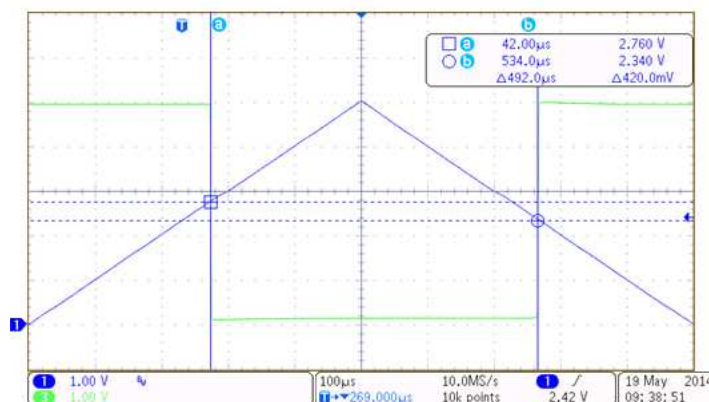


Figure 21. TLV1701 Upper and Lower Threshold With Hysteresis

9 Power Supply Recommendations

The TLV1704-SEP device is specified for operation from 2.2 V to 36 V (± 1.1 to ± 18 V); many specifications apply from -55°C to 125°C . Parameters that can exhibit significant variance with regard to operating voltage or temperature are presented in the [Typical Characteristics](#) section.

CAUTION

Supply voltages larger than 40 V can permanently damage the device; see the [Absolute Maximum Ratings](#).

Place 0.1-μF bypass capacitors close to the power-supply pins to reduce errors coupling in from noisy or high-impedance power supplies. For more detailed information on bypass capacitor placement; see the [Layout Guidelines](#) section.

10 Layout

10.1 Layout Guidelines

Comparators are very sensitive to input noise. For best results, maintain the following layout guidelines:

- Use a printed-circuit board (PCB) with a good, unbroken low-inductance ground plane. Proper grounding (use of ground plane) helps maintain specified performance of the TLV1704-SEP device.
- To minimize supply noise, place a decoupling capacitor (0.1- μ F ceramic, surface-mount capacitor) as close as possible to V_S as shown in Figure 22.
- On the inputs and the output, keep lead lengths as short as possible to avoid unwanted parasitic feedback around the comparator. Keep inputs away from the output.
- Solder the device directly to the PCB rather than using a socket.
- For slow-moving input signals, take care to prevent parasitic feedback. A small capacitor (1000 pF or less) placed between the inputs can help eliminate oscillations in the transition region. This capacitor causes some degradation to propagation delay when the impedance is low. Run the topside ground plane between the output and inputs.
- Run the ground pin ground trace under the device up to the bypass capacitor, shielding the inputs from the outputs.

10.2 Layout Example

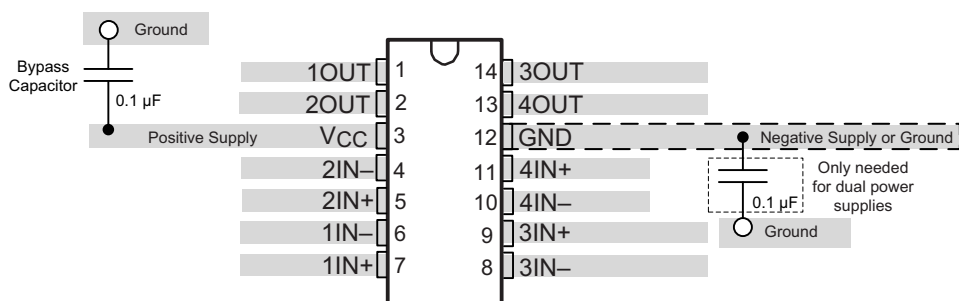


Figure 22. Comparator Board Layout

11 器件和文档支持

11.1 文档支持

11.1.1 相关文档

请参阅如下相关文档：

- 《精密设计，具有迟滞功能的比较器参考设计》，TIDU020
- 《REF33xx 3.9 μ A SC70-3、SOT-23-3 和 UQFN-8 30ppm/ $^{\circ}$ C 漂移电压基准》，SBOS392

11.2 接收文档更新通知

要接收文档更新通知，请导航至 TI.com.cn 上的器件产品文件夹。单击右上角的通知我进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

11.3 社区资源

下列链接提供到 TI 社区资源的连接。链接的内容由各个分销商“按照原样”提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的《使用条款》。

TI E2E™ 在线社区 *TI 的工程师对工程师 (E2E) 社区*。此社区的创建目的在于促进工程师之间的协作。在 e2e.ti.com 中，您可以咨询问题、分享知识、拓展思路并与同行工程师一道帮助解决问题。

设计支持 *TI 参考设计支持* 可帮助您快速查找有帮助的 E2E 论坛、设计支持工具以及技术支持的联系信息。

11.4 商标

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11.5 静电放电警告



ESD 可能会损坏该集成电路。德州仪器 (TI) 建议通过适当的预防措施处理所有集成电路。如果不遵守正确的处理措施和安装程序，可能会损坏集成电路。

ESD 的损坏小至导致微小的性能降级，大至整个器件故障。精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

11.6 术语表

SLYZ022 — *TI 术语表*。

这份术语表列出并解释术语、缩写和定义。

12 机械、封装和可订购信息

以下页面包含机械、封装和可订购信息。这些信息是指定器件的最新可用数据。数据如有变更，恕不另行通知，且不会对此文档进行修订。如需获取此数据表的浏览器版本，请查阅左侧的导航栏。

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PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TLV1704AMPWPSEP	ACTIVE	TSSOP	PW	14	90	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	1704SEP	Samples
TLV1704AMPWTPSEP	ACTIVE	TSSOP	PW	14	250	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	1704SEP	Samples
V62/18613-01XE	ACTIVE	TSSOP	PW	14	250	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	1704SEP	Samples
V62/18613-01XE-T	ACTIVE	TSSOP	PW	14	90	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-55 to 125	1704SEP	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSELETE: TI has discontinued the production of the device.

⁽²⁾ **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "-" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

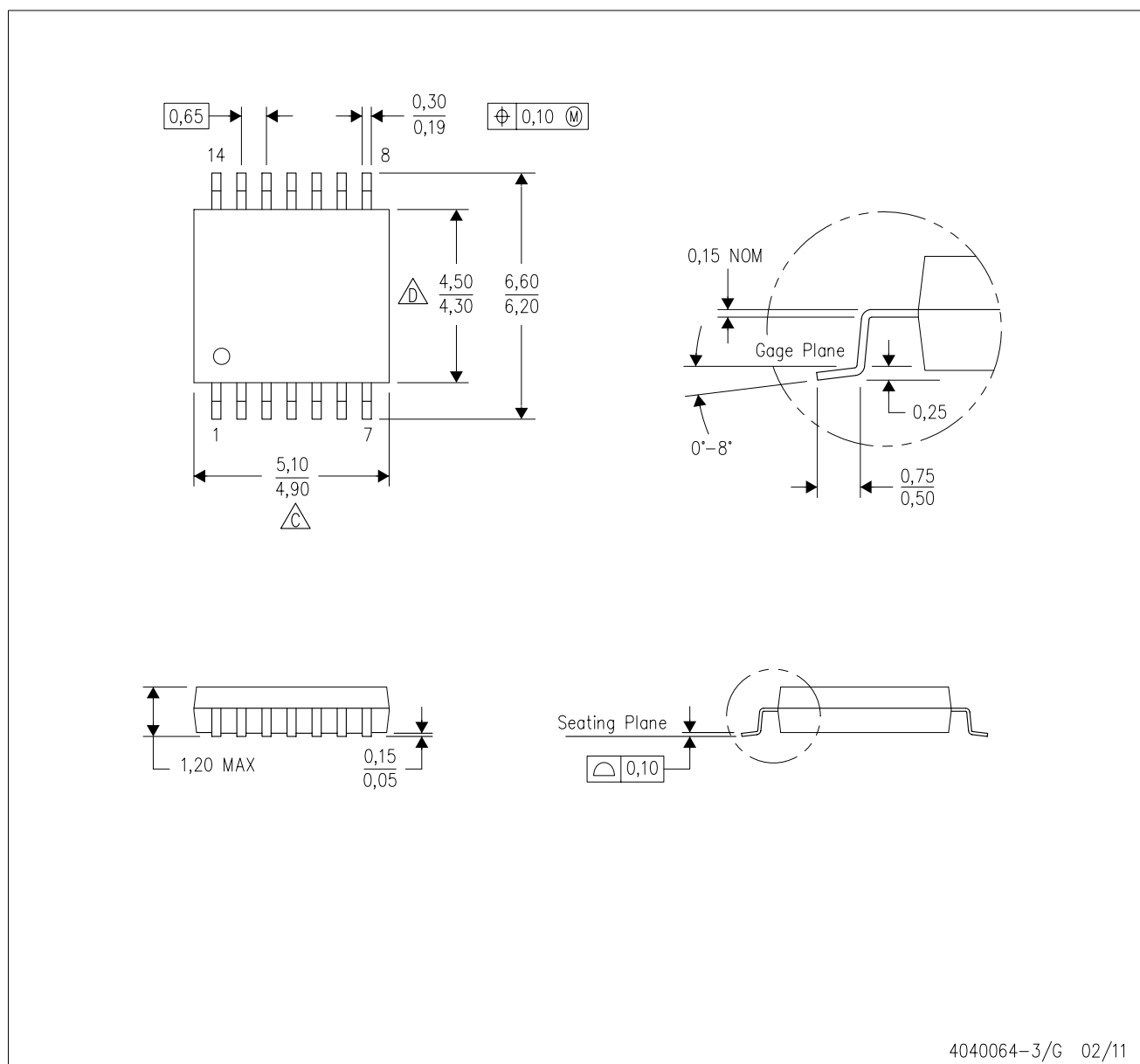
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PW (R-PDSO-G14)

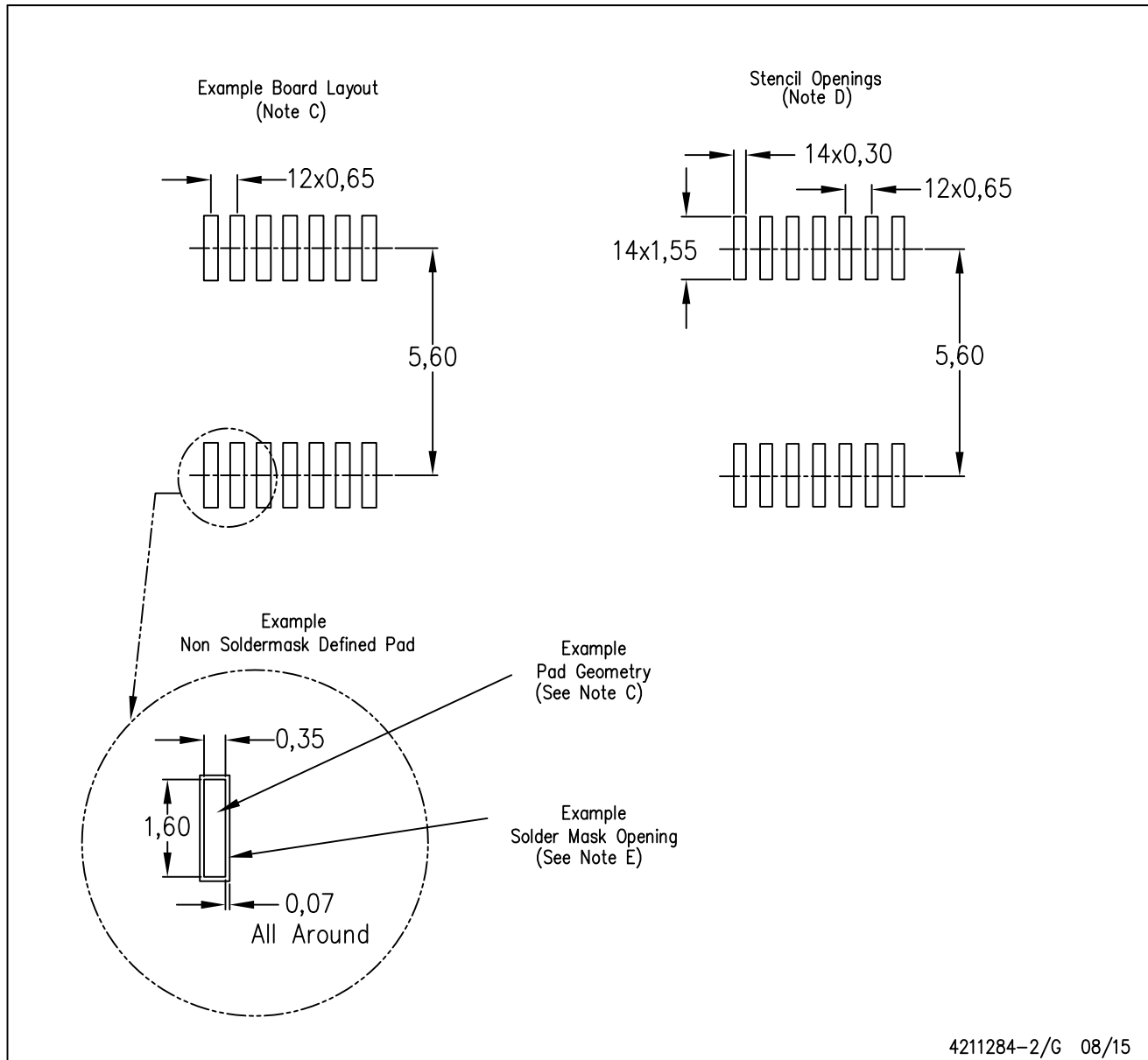
PLASTIC SMALL OUTLINE



4040064-3/G 02/11

PW (R-PDSO-G14)

PLASTIC SMALL OUTLINE



- NOTES:
- All linear dimensions are in millimeters.
 - This drawing is subject to change without notice.
 - Publication IPC-7351 is recommended for alternate designs.
 - Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
 - Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

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